

Title (en)
EPITAXIALLY COATED SEMICONDUCTOR WAFER OF MONOCRYSTALLINE SILICON AND METHOD FOR THE PRODUCTION THEREOF

Title (de)
EPITAKTISCH BESCHICHTETE HALBLEITERSCHEIBE AUS EINKRISTALLINEM SILIZIUM UND VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)
PLAQUETTE DE SEMI-CONDUCTEUR EN SILICIUM MONOCRISTALLIN, REVÊTU PAR ÉPITAXIE, ET SON PROCÉDÉ DE FABRICATION

Publication
EP 3659173 A1 20200603 (DE)

Application
EP 18740798 A 20180712

Priority
• DE 102017212799 A 20170726
• EP 2018068888 W 20180712

Abstract (en)
[origin: WO2019020387A1] Semiconductor wafer of monocrystalline silicon with a diameter of not less than 300 mm and method for producing a coated semiconductor wafer of monocrystalline silicon. The semiconductor wafer comprises a substrate wafer of monocrystalline silicon and an epitaxial layer of monocrystalline silicon that contains a dopant lying on the substrate wafer, wherein an unevenness of the thickness of the epitaxial layer is no more than 0.5% and an unevenness of the resistivity of the epitaxial layer is no more than 2%.

IPC 8 full level
H01L 21/02 (2006.01); **C23C 16/46** (2006.01); **C23C 16/48** (2006.01); **C30B 25/10** (2006.01)

CPC (source: EP IL KR US)
C23C 16/24 (2013.01 - IL US); **C23C 16/46** (2013.01 - EP IL KR); **C23C 16/481** (2013.01 - EP IL KR US); **C30B 25/08** (2013.01 - EP IL KR); **C30B 25/105** (2013.01 - EP IL KR US); **C30B 25/165** (2013.01 - EP IL KR); **C30B 25/20** (2013.01 - IL US); **C30B 29/06** (2013.01 - EP IL KR US); **C30B 29/68** (2013.01 - IL US); **H01L 21/02381** (2013.01 - EP IL KR US); **H01L 21/02532** (2013.01 - EP IL KR US); **H01L 21/0262** (2013.01 - EP IL KR US); **H01L 21/02634** (2013.01 - IL US); **H01L 27/14632** (2013.01 - IL); **H01L 27/14687** (2013.01 - IL); **H01L 29/16** (2013.01 - IL US); **H01L 27/14632** (2013.01 - US); **H01L 27/14687** (2013.01 - US)

Citation (search report)
See references of WO 2019020387A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2019020387 A1 20190131; CN 110998787 A 20200410; CN 110998787 B 20231103; DE 102017212799 A1 20190131; EP 3659173 A1 20200603; IL 271984 A 20200227; IL 271984 B 20221201; IL 271984 B2 20230401; JP 2020529127 A 20201001; JP 7059351 B2 20220425; KR 102320760 B1 20211101; KR 20200015763 A 20200212; SG 11202000675T A 20200227; TW 201910571 A 20190316; TW I672402 B 20190921; US 11578424 B2 20230214; US 2021087705 A1 20210325

DOCDB simple family (application)
EP 2018068888 W 20180712; CN 201880050070 A 20180712; DE 102017212799 A 20170726; EP 18740798 A 20180712; IL 27198420 A 20200112; JP 2020504028 A 20180712; KR 20207001195 A 20180712; SG 11202000675T A 20180712; TW 107124439 A 20180716; US 201816634178 A 20180712